

HUFA75639S3ST F085A

Data Sheet

March 2012

56A, 100V, 0.025 Ohm, N-Channel UltraFET Power MOSFETs



These N-Channel power MOSFETs are manufactured using the innovative UltraFET® process. This advanced process technology

achieves the lowest possible on-resistance per silicon area, resulting in outstanding performance. This device is capable of withstanding high energy in the avalanche mode and the diode exhibits very low reverse recovery time and stored charge. It was designed for use in applications where power efficiency is important, such as switching regulators, switching converters, motor drivers, relay drivers, low-voltage bus switches, and power management in portable and battery-operated products.

Features

- 56A, 100V
- · Peak Current vs Pulse Width Curve
- · UIS Rating Curve
- · Related Literature
 - TB334, "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUFA75639S3ST_F085A	TO263AB	75639S

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUFA75639S3ST.



Packaging



JEDEC TO-263AB

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/

Reliability data can be found at: http://www.fairchildsemi.com/products/discrete/reliability/index.html.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

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Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

		UNITS
Drain to Source Voltage (Note 1)	100	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	100	V
Gate to Source Voltage	±20	V
Drain Current		
Continuous (Figure 2)	56	Α
Pulsed Drain Current	Figure 4	
Pulsed Avalanche Rating E _{AS}	Figures 6, 14, 15	
Power Dissipation	200	W
Derate Above 25 ^o C	1.35	W/oC
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10sT _L	300	°C
Package Body for 10s, See Techbrief 334	260	°С

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST	CONDITIONS	MIN	TYP	MAX	UNITS
OFF STATE SPECIFICATIONS	!	-					-
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 11)		100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 95V, V _{GS} =	0V	-	-	1	μΑ
		V _{DS} = 90V, V _{GS} =	$0V, T_C = 150^{\circ}C$	-	-	250	μА
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
ON STATE SPECIFICATIONS							1
Gate to Source Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}$, $I_D = 2$	50μA (Figure 10)	2	-	4	V
Drain to Source On Resistance	r _{DS(ON)}	I _D = 56A, V _{GS} = 10	OV (Figure 9)	-	0.021	0.025	Ω
THERMAL SPECIFICATIONS							1
Thermal Resistance Junction to Case	$R_{ heta JC}$	(Figure 3)		-	-	0.74	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-247		-	-	30	oC/W
		TO-220, TO-263		-	-	62	oC/W
SWITCHING SPECIFICATIONS (V _{GS} = 10)	/)						1
Turn-On Time	ton	$V_{DD} = 50V, I_{D} = 56A,$ $R_{L} = 0.89\Omega, V_{GS} = 10V,$ $R_{GS} = 5.1\Omega$		-	-	110	ns
Turn-On Delay Time	t _d (ON)			-	15	-	ns
Rise Time	t _r			-	60	-	ns
Turn-Off Delay Time	t _d (OFF)			-	20	-	ns
Fall Time	t _f			-	25	-	ns
Turn-Off Time	tOFF			-	-	70	ns
GATE CHARGE SPECIFICATIONS	II.						
Total Gate Charge	Q _{g(TOT)}	$V_{GS} = 0V \text{ to } 20V$	$V_{DD} = 50V,$ $I_{D} \cong 56A,$ $R_{L} = 0.89\Omega$	-	110	130	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V		-	57	75	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V	$I_{g(REF)} = 1.0 \text{mA}$	-	3.7	4.5	nC
Gate to Source Gate Charge	Q _{gs}		(Figure 13)	-	9.8	-	nC
	Q _{gd}	†			24		nC

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Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
CAPACITANCE SPECIFICATIONS						
Input Capacitance	C _{ISS}	$V_{DS} = 25V, V_{GS} = 0V,$	-	2000	-	pF
Output Capacitance	C _{OSS}	f = 1MHz (Figure 12)	1	500	-	pF
Reverse Transfer Capacitance	C _{RSS}		-	65	-	pF

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	I _{SD} = 56A	-	-	1.25	V
Reverse Recovery Time	t _{rr}	$I_{SD} = 56A$, $dI_{SD}/dt = 100A/\mu s$	-	-	110	ns
Reverse Recovered Charge	Q _{RR}	$I_{SD} = 56A$, $dI_{SD}/dt = 100A/\mu s$	-	-	320	nC

Typical Performance Curves

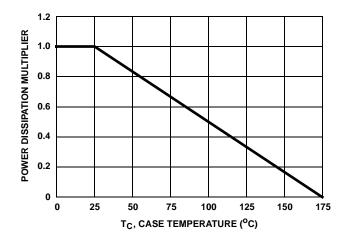


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

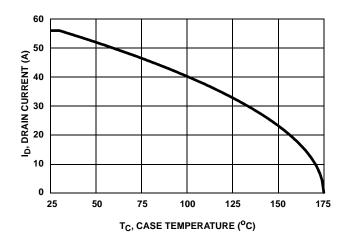


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

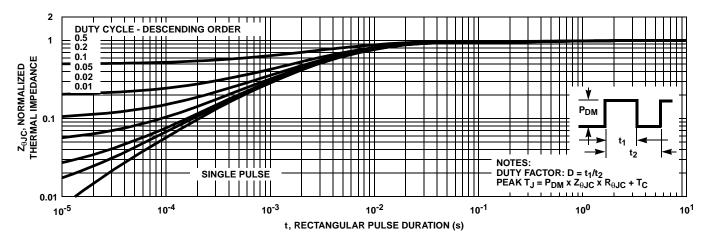


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

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Typical Performance Curves (Continued)

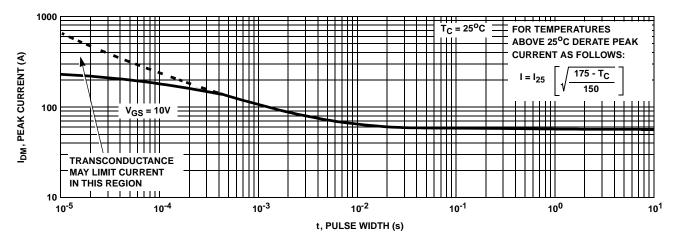


FIGURE 4. PEAK CURRENT CAPABILITY

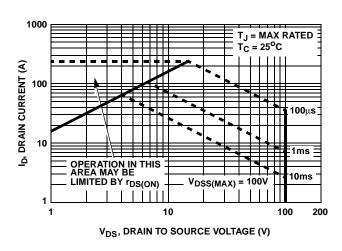


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA

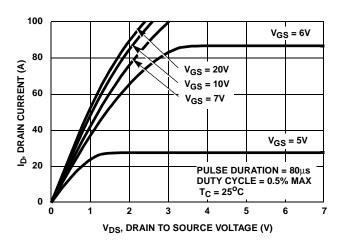
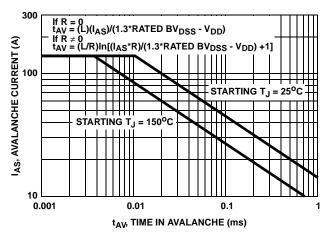


FIGURE 7. SATURATION CHARACTERISTICS



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

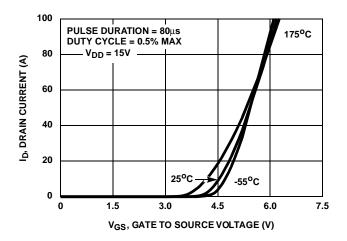


FIGURE 8. TRANSFER CHARACTERISTICS

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Typical Performance Curves (Continued)

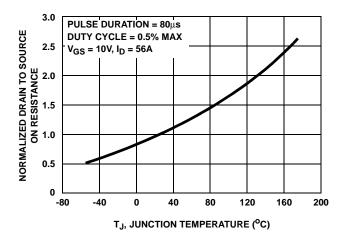


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

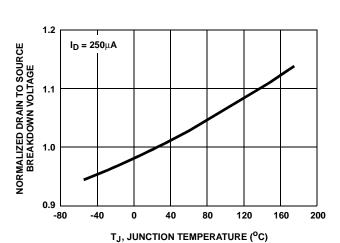


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

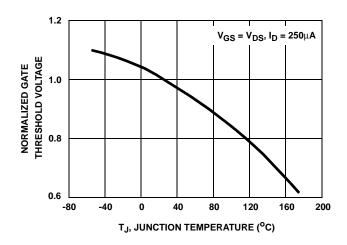


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

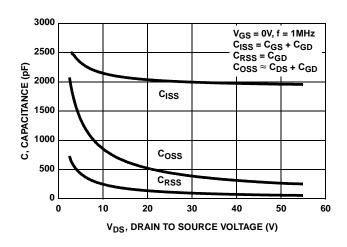
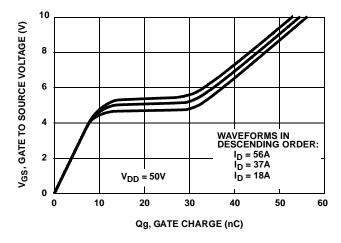


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

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Test Circuits and Waveforms

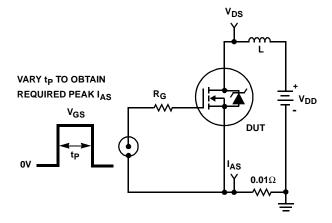


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

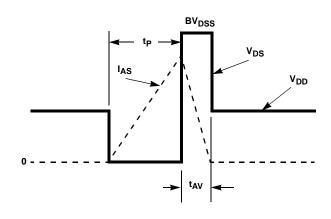


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

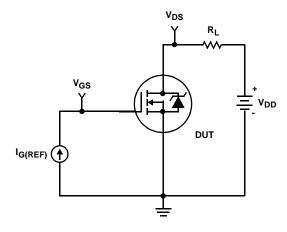


FIGURE 16. GATE CHARGE TEST CIRCUIT

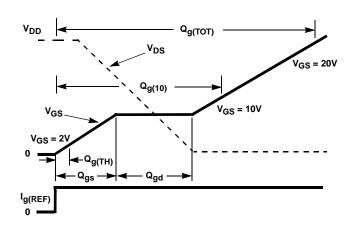


FIGURE 17. GATE CHARGE WAVEFORM

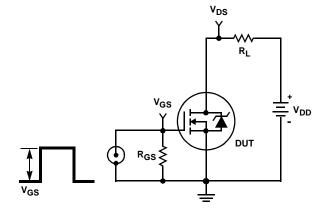


FIGURE 18. SWITCHING TIME TEST CIRCUIT

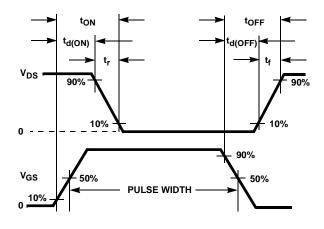


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

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